

IN THE SPECIFICATION:

Please amend paragraph number [0008] as follows:

[0008] What is needed is a way to combine the beneficial qualities of both ~~reactively sputtered~~ reactively sputtered titanium nitride with those of titanium nitride deposited via LPCVD.

Please amend paragraph number [0010] as follows:

[0010] FIG. 1, a cross-sectional view of a portion of an in-process semiconductor wafer, depicts a portion of a dynamic random access memory (DRAM) array following field oxidation, ~~wordline~~ word line formation, source/drain implants, deposition of a thick dielectric layer, and polysilicon plug formation;

Please amend paragraph number [0016] as follows:

[0016] Referring now to FIG. 1, a portion of an in-process dynamic random access memory (DRAM) array is shown following a field oxidation step which formed field oxide regions 11, the deposition and patterning of a polysilicon layer to form ~~wordlines~~ word lines WL1-WL4, source/drain implants which have formed storage-node junctions 12 and bit line contact junctions 13, the deposition of a thick, flowable dielectric layer (e.g., borophosphosilicate glass) 14 which covers substrate-superadjacent topography such as ~~wordlines~~ word lines and field oxide regions, the formation of contact openings 15 in the thick dielectric layer 14 which expose the storage-node junctions 12, filling the contact openings 15 with polysilicon material, and planarization of the wafer to form polysilicon plugs 16.